IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-13. (Canceled)

14. (Currently Amended) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the first semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the semiconductor film;

forming an island-like semiconductor film by removing a part of the first semiconductor film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a contact hole is formed by removing at least a part of the gate insulating film over [[the]]a gate electrode of the second semiconductor element; and a wiring for connecting the source electrode or the drain electrode of the first semiconductor element to the gate electrode of the second semiconductor element is formed by discharging a composite containing a third conductive material via the contact hole.

15. (Currently Amended) A method for manufacturing a light-emitting device having, at

least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the first semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the first semiconductor film;

forming an island-like semiconductor film and an island-like gate insulating film by removing a part of the first semiconductor film and a part of the gate insulating film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a contact hole is formed by removing at least a part of the gate insulating film over [[the]]a gate electrode of the second semiconductor element; and a wiring for connecting the source electrode or the drain electrode of the first semiconductor element to the gate electrode of the second semiconductor element is formed by discharging a composite containing a third conductive material via the contact hole.

16. (Currently Amended) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the first semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the first semiconductor film;

forming an island-like semiconductor film by removing a part of the first semiconductor film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a column-like conductor is formed by discharging a composite containing a third conductive material which is the same or different from the first conductive material above a part of a gate electrode of the second semiconductor element before forming the gate insulating film; and a wiring for connecting the source electrode or the drain electrode of the first semiconductor element to the column-like conductor is formed by discharging a composite containing a fourth conductive material.

17. (Currently Amended) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the first semiconductor film;

forming an island-like semiconductor film and an island-like gate insulating film by removing a part of the first semiconductor film and a part of the gate insulating film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a column-like conductor is formed by discharging a composite containing a third conductive material which is the same or different from the first conductive material above a part of a gate electrode of the second semiconductor element before forming the gate insulating film; and a wiring for connecting the source electrode or the drain electrode of the first semiconductor element to the column-like conductor is formed by discharging a composite containing a fourth conductive material.

18. (Currently Amended) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the first semiconductor film;

forming an island-like semiconductor film by removing a part of the first semiconductor film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a wiring is formed by discharging a composite containing a third conductive material so as to be in contact with the source electrode or the drain electrode of the first semiconductor element; a contact hole is formed by removing at least a part of the gate insulating film over a gate electrode of the second semiconductor element using the wiring as a mask; and a conductor for connecting the wiring to the gate electrode of the second semiconductor element is formed by discharging a composite containing a fourth conductive material over the contact hole.

19. (Currently Amended) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a first semiconductor film over the gate insulating film;

forming a second semiconductor film containing an impurity element having a conductivity type over the semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the second semiconductor film;

forming a source region and a drain region by removing a part of the second semiconductor film using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the first semiconductor film;

forming an island-like semiconductor film and an island-like gate insulating film by removing a part of the first semiconductor film and a part of the gate insulating film using the source electrode, the drain electrode, and the insulating film as a mask;

wherein a wiring which is in contact with the source electrode or the drain electrode is formed by discharging a composite containing a third conductive material so as to be in contact

with the source electrode or the drain electrode of the first semiconductor element; a contact hole is formed by removing at least a part of the gate insulating film over a gate electrode of the second semiconductor element using the wiring as a mask; and a conductor for connecting the wiring to the gate electrode of the second semiconductor element is formed by discharging a composite containing a fourth conductive material over the contact hole.

20. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 14, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

21. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 15, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

22. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 16, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

23. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 17, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

24. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 18, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

25. (Previously Presented) A method for manufacturing a light-emitting device according to Claim 19, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

26. (Previously Presented) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 14.

27. (Previously Presented) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 15.

28. (Previously Presented) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 16.

29. (Previously Presented) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 17.

30. (Previously Presented) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 18.

31. (Previously Presented) An electroluminescent television device having a light-

emitting device manufactured by the method for manufacturing according to Claim 19.

32-33. (Canceled)

34. (Previously Presented) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a semiconductor film over the gate insulating film;

forming a semiconductor film containing an impurity element having a conductivity type over the semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the semiconductor film containing a single conductivity impurity element;

forming a source region and a drain region by removing a part of the semiconductor film containing a single conductivity impurity element using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the semiconductor film;

forming an island-like semiconductor film by removing a part of the semiconductor film using the source electrode, the drain electrode, and the insulating film as a mask.

35. (Previously Presented) A method for manufacturing a light-emitting device having, at least a first semiconductor element and a second semiconductor element in one pixel of the light-emitting device, said method comprising the steps of:

forming a gate electrode by discharging a composite containing a first conductive material over a substrate;

forming a gate insulating film over the gate electrode ;

forming a semiconductor film over the gate insulating film;

forming a semiconductor film containing an impurity element having a conductivity type over the semiconductor film;

forming a source electrode and a drain electrode by discharging a composite containing a second conductive material over the semiconductor film containing an impurity element having a conductivity type;

forming a source region and a drain region by removing a part of the semiconductor film containing an impurity element having a conductivity type using the source electrode and the drain electrode as a mask;

forming an insulating film above a portion serving as a channel region in the semiconductor film;

forming an island-like semiconductor film and an island-like gate insulating film by removing a part of the semiconductor film using the source electrode, the drain electrode, and the insulating film as a mask.

36. (New) A method for manufacturing a light-emitting device according to Claim 34, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl group, and aromatic hydrocarbon as the substituent.

37. (New) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 34.

38. (New) A method for manufacturing a light-emitting device according to Claim 35, wherein the insulating film comprises a material selected from the group consisting of polyimide, acrylic, or a material which has a bond of silicon and oxygen, and which includes at least hydrogen as a substituent, or at least one selected from the group consisting of fluoride, alkyl

group, and aromatic hydrocarbon as the substituent.

39. (New) An electroluminescent television device having a light-emitting device manufactured by the method for manufacturing according to Claim 35.